## Ziyu Zhao

## List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/7328216/publications.pdf

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13	195	6	11
papers	citations	h-index	g-index
13	13	13	201
all docs	docs citations	times ranked	citing authors

#	Article	IF	CITATIONS
1	Quantitative SERS sensing mediated by internal standard Raman signal from silica nanoparticles in flexible polymer matrix. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2022, 278, 121304.	3.9	4
2	SERS-based immunoassay and degradation of CA19-9 mediated by gold nanowires anchored magnetic–semiconductor nanocomposites. Journal of Hazardous Materials, 2021, 403, 124009.	12.4	45
3	Highâ€voltage AllnN/GaN superjunction finâ€gate high electron mobility transistor for powerâ€switching application. Micro and Nano Letters, 2021, 16, 363.	1.3	0
4	Immunoassay of Tumor Markers Based on Graphene Surface-Enhanced Raman Spectroscopy. ACS Applied Bio Materials, 2020, 3, 8012-8022.	4.6	17
5	Sandwich Au/SMSiO2/Ag hybrid substrate: synthesis, characterization, and surface-enhanced Raman scattering performance. Journal of Nanoparticle Research, 2020, 22, 1.	1.9	5
6	Recyclable SERS-Based Immunoassay Guided by Photocatalytic Performance of Fe3O4@TiO2@Au Nanocomposites. Biosensors, 2020, 10, 25.	4.7	22
7	Quantitative and Recyclable Surface-Enhanced Raman Spectroscopy Immunoassay Based on Fe <sub>3</sub> O <sub>4</sub> @TiO <sub>2</sub> @Ag Core–Shell Nanoparticles and Au Nanowire/Polydimethylsiloxane Substrates. ACS Applied Nano Materials, 2020, 3, 4610-4622.	5.0	30
8	Hollow Ag dendritic nanoplates with serrated inner surfaces for sensitive SERS-based detection. Materials Research Express, 2019, 6, 105053.	1.6	4
9	Theoretical investigation of high-voltage superjunction GaN-based vertical hetero-junction field effect transistor with ununiformly doped buffer to suppress charge imbalance effect. Semiconductor Science and Technology, 2019, 34, 065012.	2.0	4
10	Numerical analysis of highâ€voltage RESURF AlGaN/GaN highâ€electronâ€mobility transistor with graded doping buffer and slant back electrode. Micro and Nano Letters, 2019, 14, 1282-1286.	1.3	0
11	A Vacancy-Interstitial Defect Pair Model for Positive-Bias Temperature Stress-Induced Electron Trapping Transformation in the High- \$kappa \$ Gate n-MOSFET. IEEE Transactions on Electron Devices, 2017, 64, 2505-2511.	3.0	4
12	Hydrothermal synthesis of Ag@MSiO <sub>2</sub> @Ag three core–shell nanoparticles and their sensitive and stable SERS properties. Nanoscale, 2016, 8, 4908-4914.	5.6	49
13	Highâ€voltage RESURF AlGaN/GaN high electron mobility transistor with back electrode. Electronics Letters, 2013, 49, 1638-1640.	1.0	11